onsemi

RF Amplifier, N-Channel

MMBF4416A

Features

- This Device is Designed for RF Amplifiers
- Sourced from Process 50
- This is a Pb–Free and Halide Free Device

ABSOLUTE MAXIMUM RATINGS

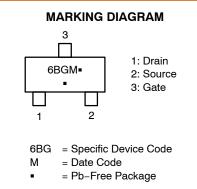
 $(T_A = 25^{\circ}C \text{ unless otherwise noted.})$ (Notes 1, 2)

Symbol	Parameter	Value	Unit
V _{DG}	Drain-Gate Voltage	35	V
V _{GS}	Gate-Source Voltage	-35	V
I _{GF}	Forward Gate Current	10	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

These ratings are based on a maximum junction temperature of 150°C.
These are steady-state limits. **onsemi** should be consulted on applications involving pulsed or low-duty-cycle operations.

SOT-23 CASE 318BM



ORDERING INFORMATION

Device	Package	Shipping [†]
MMBF4416A	SOT–23 (Pb–Free/ Halide Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please

refer to our Tape and Reel Packaging Specification Brochure, <u>BRD8011/D</u>.

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THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted.})$ (Note 3)

Symbol	Parameter	Max	Unit
PD	Total Device Dissipation Derate above 25°C	225 1.8	mW mW/°C
R_{\thetaJA}	Thermal Resistance, Junction-to-Ambient	556	°C/W

3. Device mounted on FR-4 PCB $1.6'' \times 1.6'' \times 0.06''.$

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted.)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
OFF CHAR	ACTERISTICS					
V _{(BR)GSS}	Gate-Source Breakdown Voltage	$V_{DS} = 0, I_G = 1.0 \ \mu A$	-35	-	-	V
I _{GSS}	Gate Reverse Current	$V_{GS} = -20 \text{ V}, V_{DS} = 0$	-	-	-100	pА
V _{GS} (off)	Gate-Source Cut-off Voltage	V _{DS} = 15 V, I _D = 1.0 nA	-2.5	-	-6.0	V
V _{GS}	Gate-Source Voltage	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 500 \ \mu\text{A}$	-1.0	-	-5.5	V
ON CHARA	ACTERISTICS					
I _{DSS}	Zero-Gate Voltage Drain Current	$V_{GS} = 15 \text{ V}, V_{GS} = 0$	5	-	15	mA
V _{GS} (f)	Gate-Source Forward Voltage	$V_{DS} = 0, I_G = 1.0 \text{ mA}$	_	-	1	V
SMALL SIG	SNAL CHARACTERISTICS					
9 _{fs}	Forward Transfer Admittance (Note 4)	$V_{DS} = 15 \text{ V}, \text{ V}_{GS} = 0, \text{ f} = 1.0 \text{ kHz}$	4500	-	7500	μmhos
g _{os}	Output Admittance (Note 4)	V_{DS} = 15 V, V_{GS} = 0, f = 1.0 kHz	-	-	50	μmhos
C _{iss}	Input Capacitance	$V_{DS} = 15 \text{ V}, \text{ V}_{GS} = 0, \text{ f} = 1.0 \text{ MHz}$	-	-	4.0	pF
C _{rss}	Reverse Transfer Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0, \text{ f} = 1.0 \text{ MHz}$	-	-	0.8	pF
C _{oss}	Output Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0, \text{ f} = 1.0 \text{ MHz}$	-	-	2.0	pF
NF	Noise Figure	V_{DS} = 15 V, V_{GS} = 0, I_D = 5 mA, R_g = 1 k $\Omega,$ f = 400 MHz	-	_	4.0	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 4. Pulse test: pulse width \leq 300 ms, duty cycle \leq 2%

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